**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020M-6 (SOT1220-2) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

## 3. Applications

- · Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- · Computing power management

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V	
$V_{GS}$	gate-source voltage			-8	-	8	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-17.5	Α	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -12.5 \text{ A}; T_j = 25 \text{ °C}$		-	7.3	8.6	mΩ	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 1 6	D
2	D	drain	7 7	
3	G	gate	2         5	G (F)
4	S	source	3 8 4	s
5	D	drain	Transparent top view	017aaa094
6	D	drain	DFN2020M-6 (SOT1220-2)	
7	D	drain		
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PMPB07R3VP		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1220-2				

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PMPB07R3VP	ZK

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-17.5	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-12.5	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-7.9	А
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-50	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T <sub>amb</sub> = 25 °C	[1]	-	1.9	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	iode		·			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

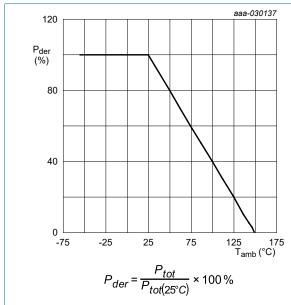


Fig. 1. Normalized total power dissipation as a function of ambient temperature

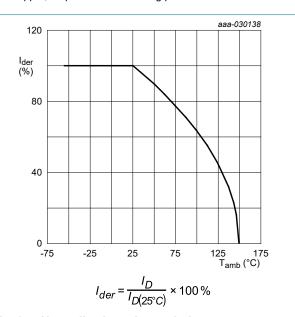


Fig. 2. Normalized continous drain current as a function of ambient temperature

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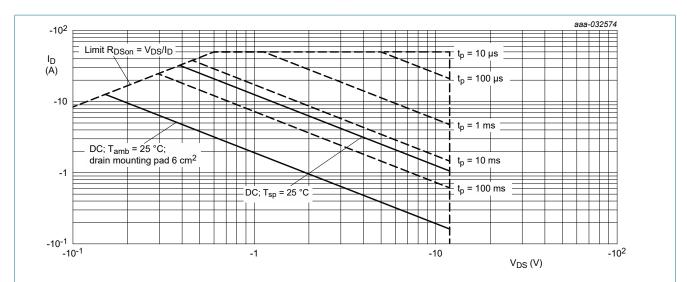


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

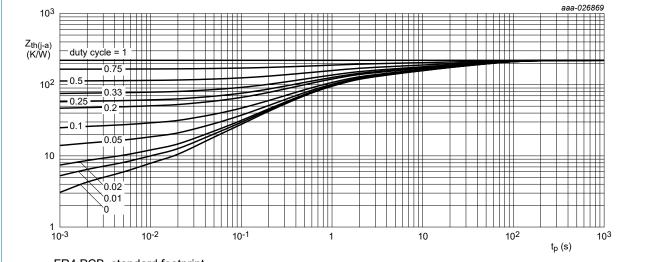
12 V, P-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air [	[1]	-	223	256	K/W
	junction to ambient		[2]	-	57	66	K/W
		in free air, t ≤ 5 s	[2]	-	29	33	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	6	10	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

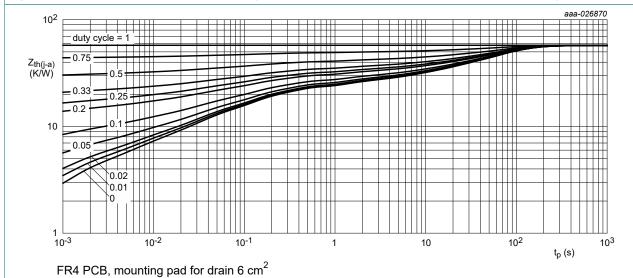


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.47	-0.65	-0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -12.5 \text{ A}; T_j = 25 \text{ °C}$	-	7.3	8.6	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -12.5 A; T <sub>j</sub> = 150 °C	-	10	12	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -8 \text{ A}; T_j = 25 \text{ °C}$	-	9.2	12	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C	-	12	19	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -12.2 A; $T_j$ = 25 °C	-	30	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	17	-	Ω
Dynamic ch	aracteristics		·			·
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -6 V; I <sub>D</sub> = -12.2 A; V <sub>GS</sub> = -4.5 V;	-	28	40	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	3.1	-	nC
$Q_{GD}$	gate-drain charge		-	7.4	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -6 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	2121	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	511	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	462	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -6 V; I <sub>D</sub> = -12.2 A; V <sub>GS</sub> = -4.5 V;	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	201	-	ns
t <sub>f</sub>	fall time	1	-	120	-	ns
Source-drai	in diode			<u>'</u>	<u> </u>	1
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -1.8 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.6	-1.2	V

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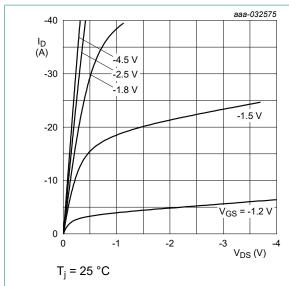


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

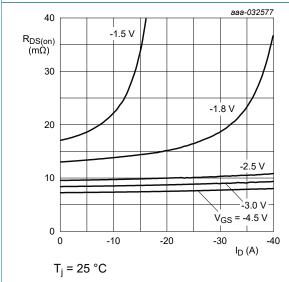


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

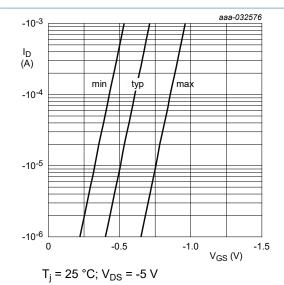


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

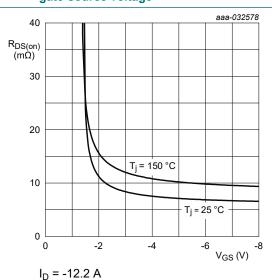


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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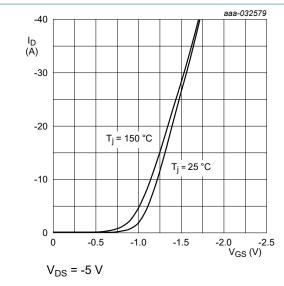


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

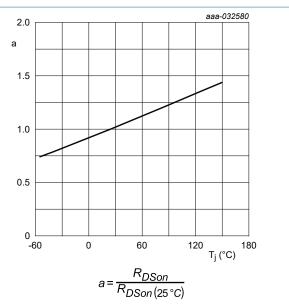


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

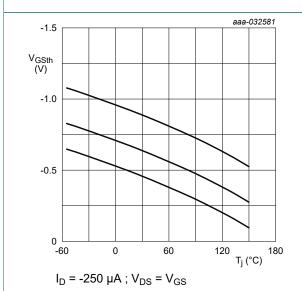


Fig. 12. Gate-source threshold voltage as a function of junction temperature

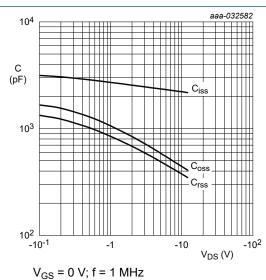


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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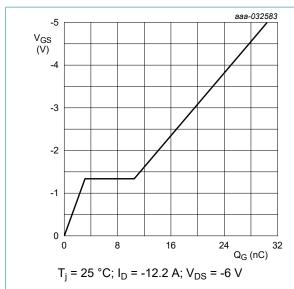


Fig. 14. Gate-source voltage as a function of gate charge; typical values

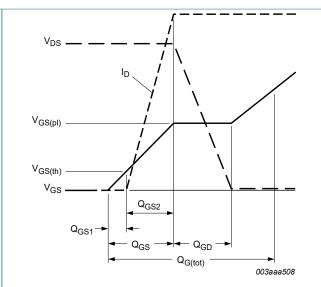


Fig. 15. Gate charge waveform definitions

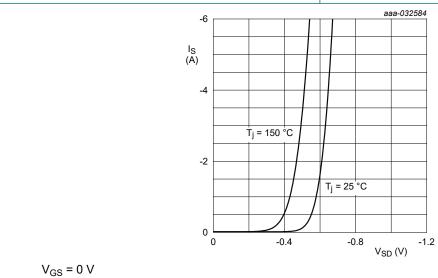
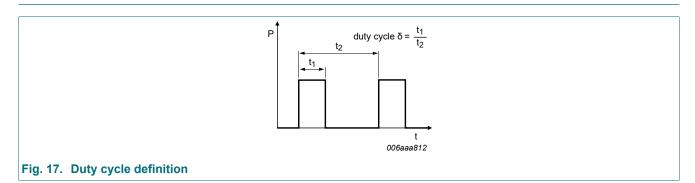


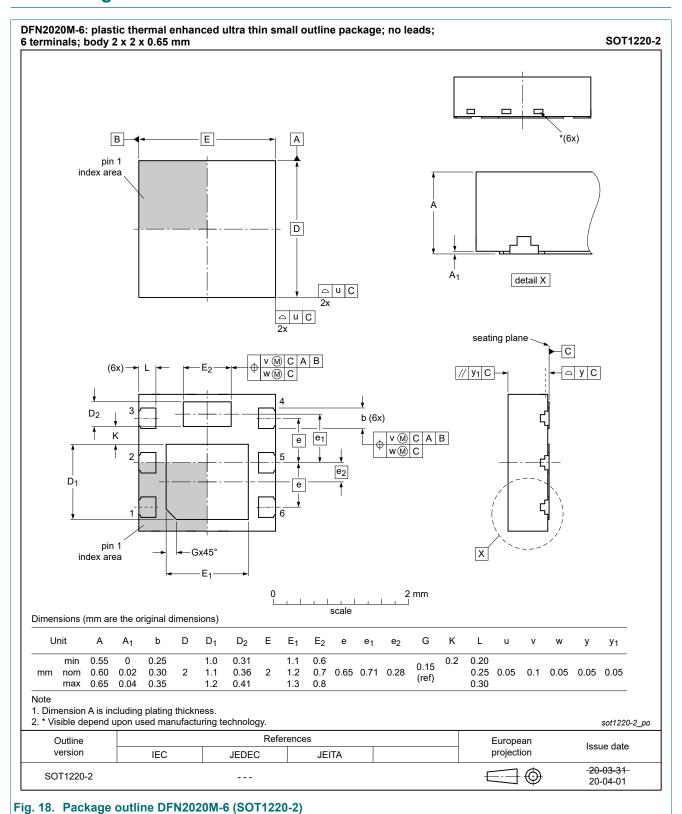
Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



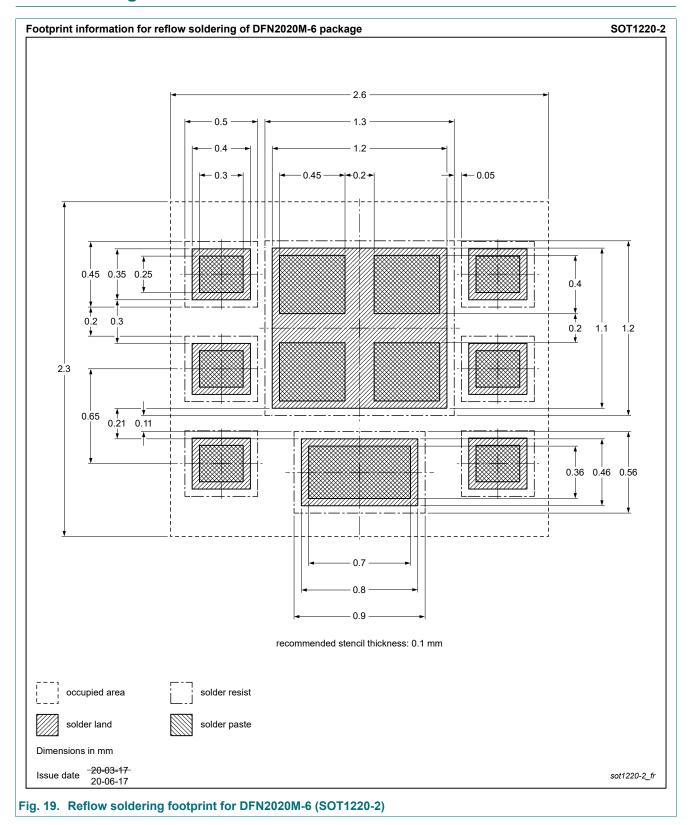
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# 12. Package outline



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# 13. Soldering



12 V, P-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB07R3VP v.1	20210301	Product data sheet	-	-

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### 12 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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